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**FULL SIMULATIONS OF BEAM DYNAMICS OF CRYSTAL-BASED
EXTRACTION FROM THE DESY II BOOSTER SYNCHROTRON
USING BDSIM SIMULATION CODE BOOSTED WITH
G4CHANNELINGFASTSIMMODEL**

Channeling 2024

Riccione, 10/09/24

Marie Skłodowska-Curie Action Global Individual Fellowships by A. Sytov in 2021-2024, Project TRILLION GA n. 101032975

Main goal: The **implementation** of both physics of **electromagnetic processes in oriented crystals** and the design of specific applications of crystalline effects into **Geant4** simulation toolkit as Extended Examples to bring them to a large scientific and industrial community and under a free Geant4 license.

Group:

- **A. Sytov** – project coordinator
- **L. Bandiera** – INFN supervisor
- **K. Cho** – KISTI supervisor
- **G. Kube** – DESY supervisor
- **I. Chaikovska** – IJCLab Orsay supervisor

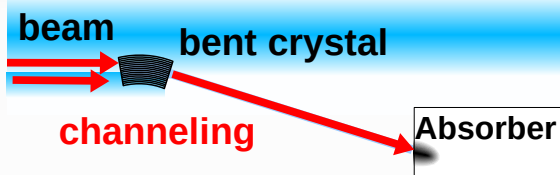
Location:

- 2 years at **KISTI** (partner organization)
- 1 year at **INFN Section of Ferrara** (host organization)
- **1 month of secondment at DESY** (partner organization)
- 1 month of secondment at **IJCLab Orsay** (partner organization)

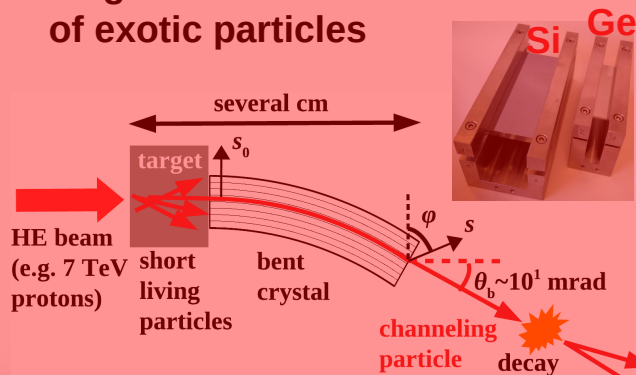


Applications*

Crystal-based beam extraction from an accelerator

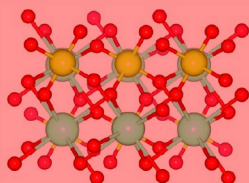


Measurement of dipole magnetic and electric moments of exotic particles

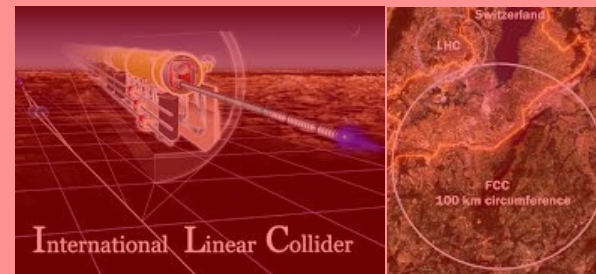
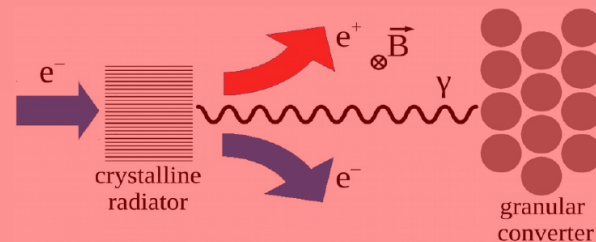


Gamma-ray Space Telescope

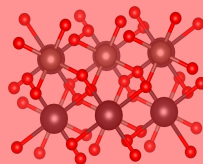
Ultrashort crystalline calorimeter



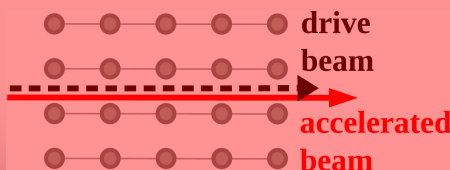
Positron source for future e⁺/e⁻ and muon colliders



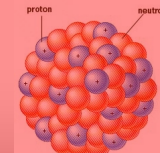
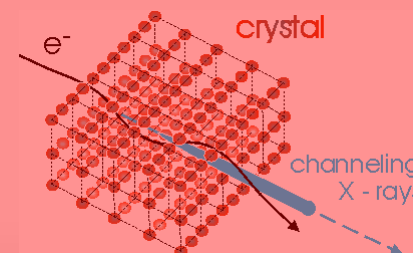
Oriented crystals



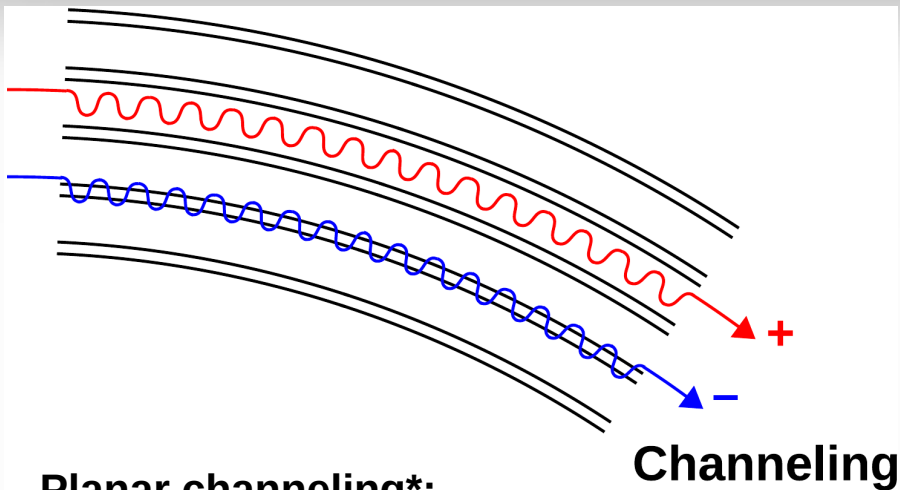
Plasma acceleration



X and gamma-ray source for nuclear and medical physics



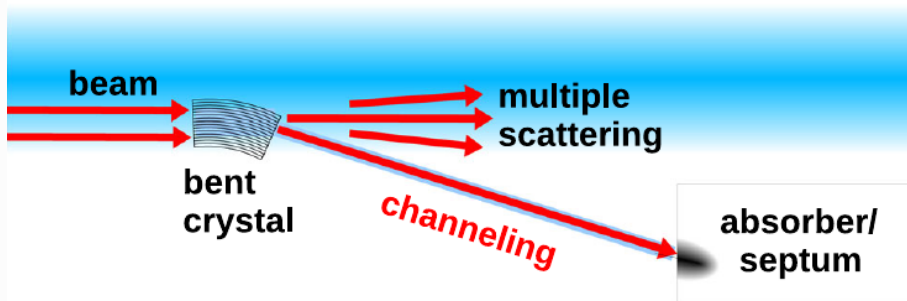
Crystal-based extraction: the idea



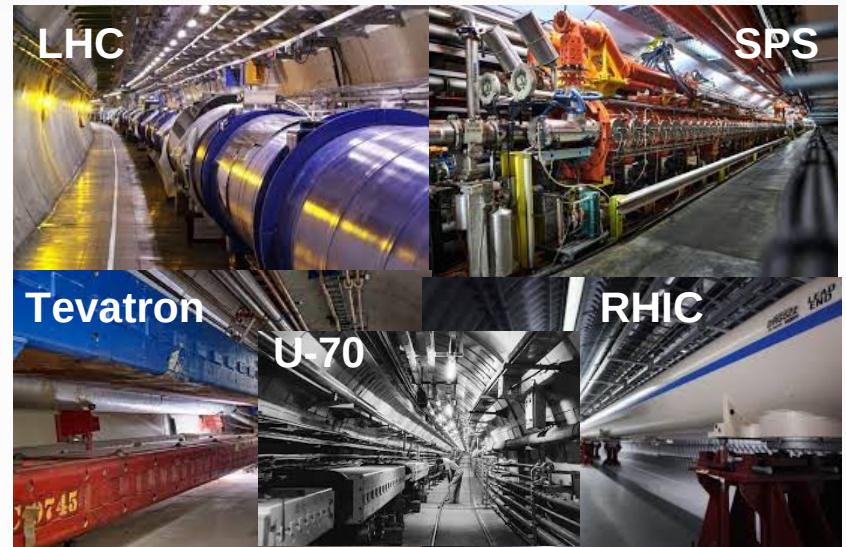
Planar channeling*:

● Charge particle penetration through a monocrystal along its atomic planes

Crystal-based extraction/collimation



Crystal-based collimation and extraction have been used at hadron machines



Crystal-based extraction/collimation: applied only for hadrons, not yet for e-

Interesting for tens of electron synchrotrons

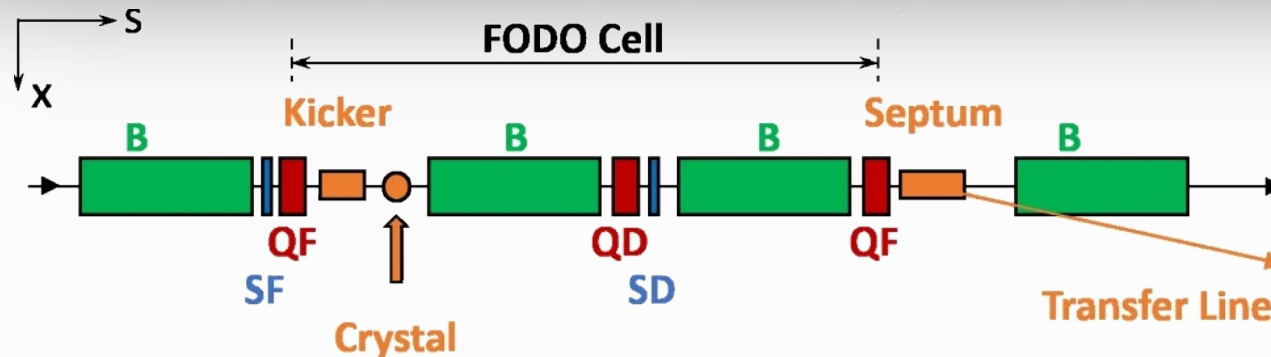


*J. Lindhard, Kgl. Dan. Vid. Selsk. Mat.-Fys. Medd. 34 No 4, 2821–2836 (1965)

E.N. Tsyganov, Fermilab TM-682 (1976)

A. Sytov et al. Eur. Phys. J. C 82, 197 (2022)

Crystal-based extraction: possible setup at DESY-II



B->dipoles
QF/QD->focusing/
defocusing quadrupoles

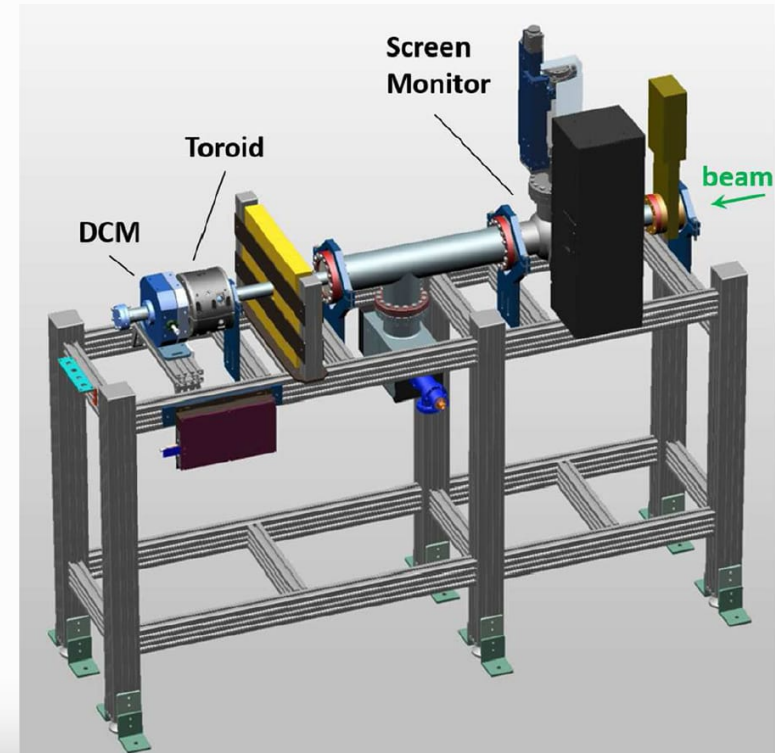
6 GeV electrons

Advantages:

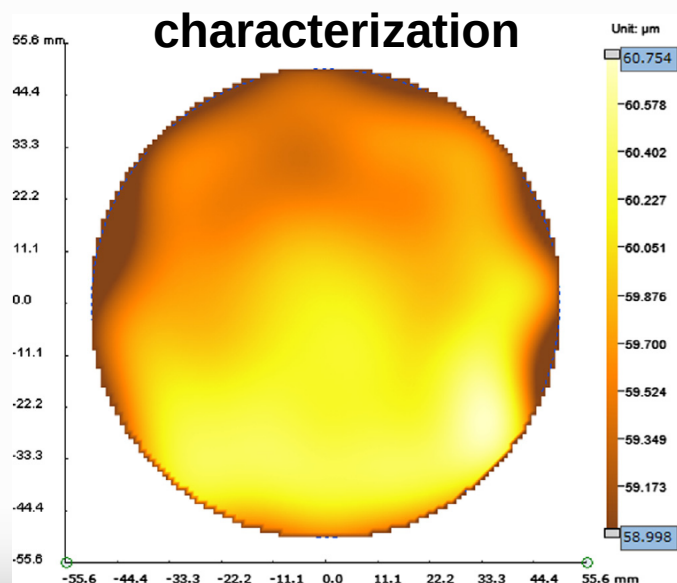
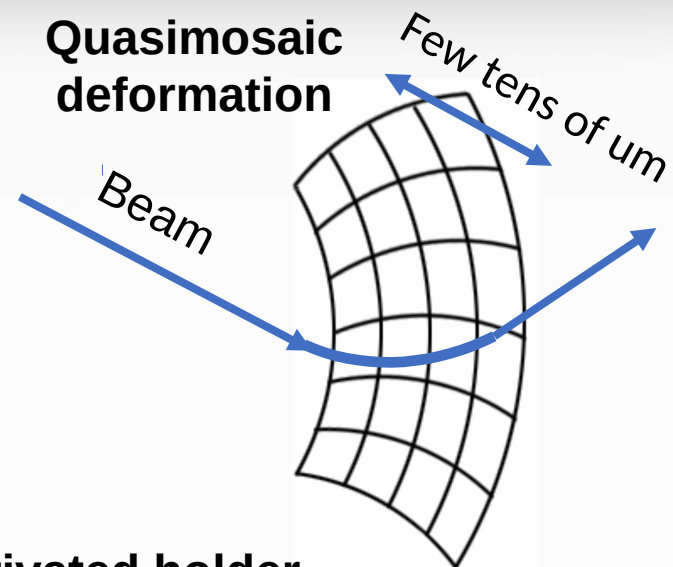
- Extraction of **primary** low-emittance and very **intense electron beam** in a **parasitic mode**.
- The **extraction line** including septum magnets already **exists** => **ideal for prove-of-principle**
- **Few GeV** electron beam, **typical** for **synchrotron light sources** existing in the world.

Applications:

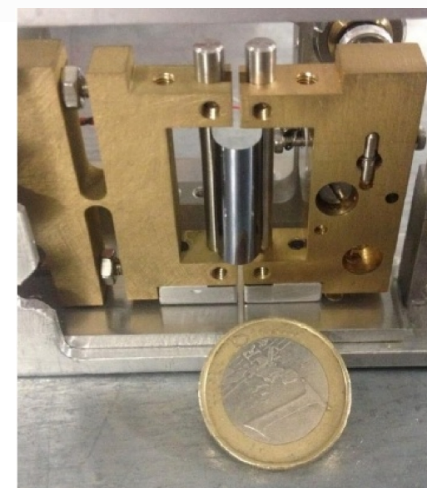
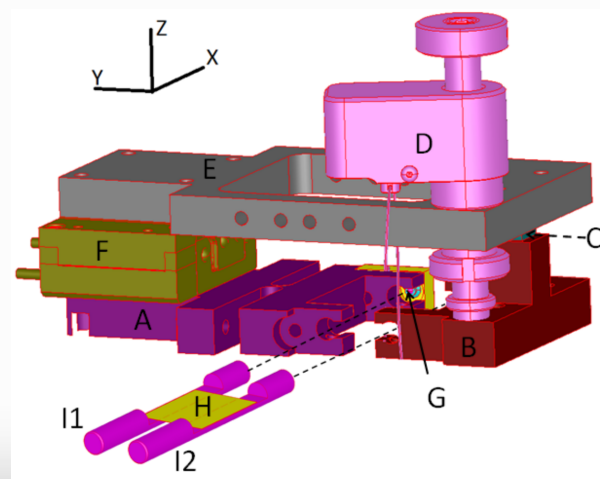
- Nuclear and particle physics detectors and generic **detector R&D**
- Fixed-target experiments in **high-energy physics** including future **lepton colliders**
- Also: **crystal-based collimation** (synchrotron light sources, colliders)



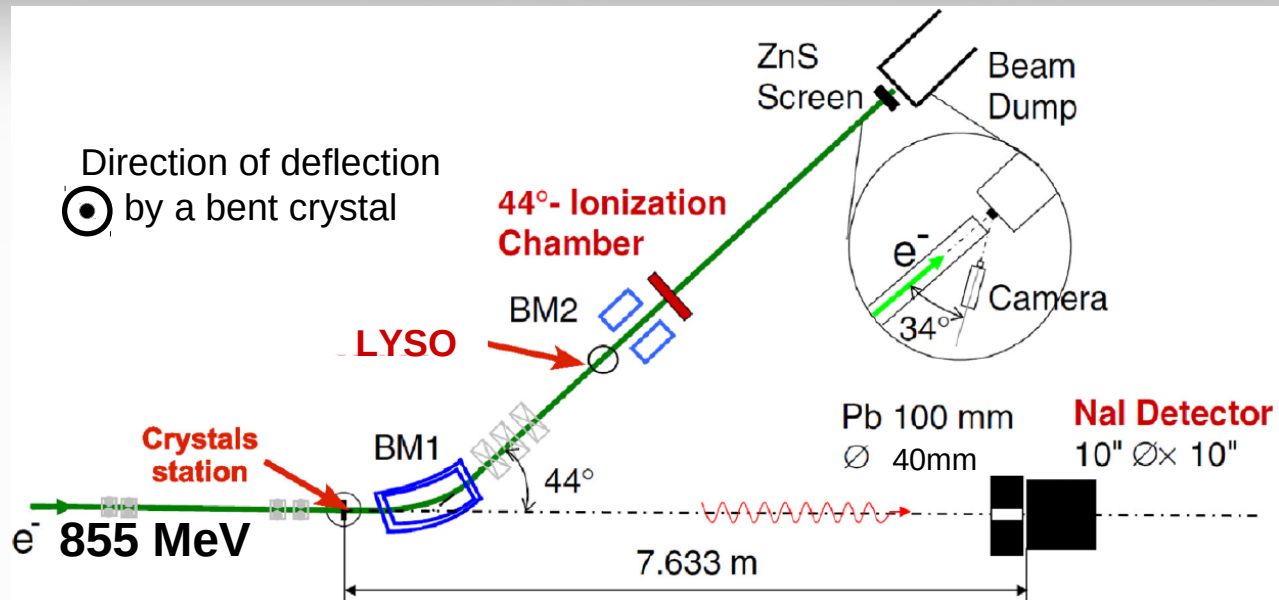
Manufacturing and characterization of bent silicon crystals @INFN Ferrara



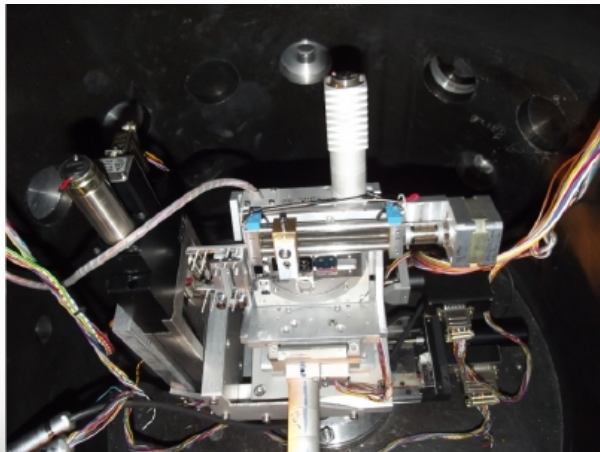
Piezo-activated holder



Experimental setup at Mikrotron MAMI



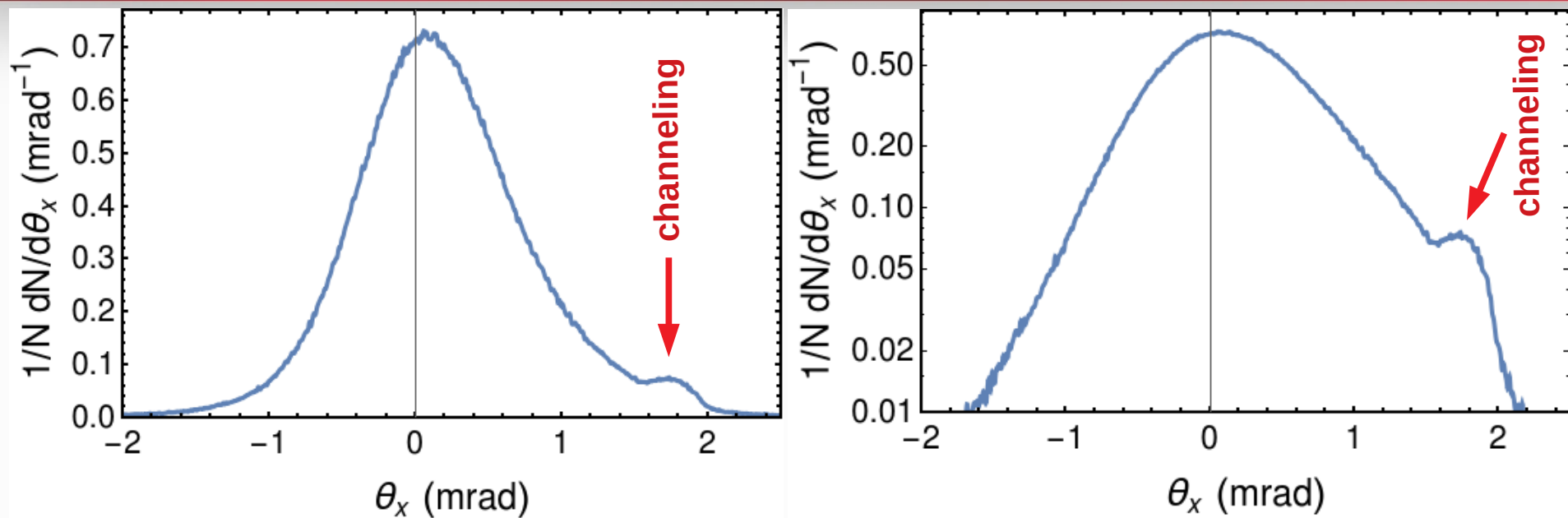
Crystal station



Detector station



Crystal characterization: simulations of the deflection of 855 MeV electrons at Mainz Mikrotron MAMI

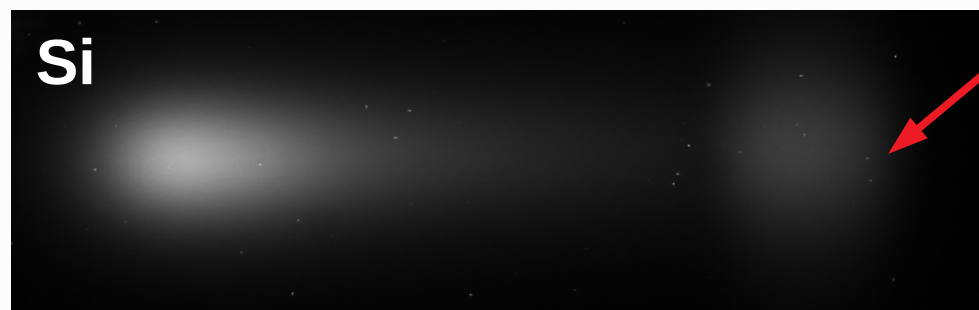


LYSO screen photo example

channeling

Simulation parameters:

- 855 MeV electrons
- Si (111)
- bending angle 1.75 mrad
- Crystal length 0.175 mm

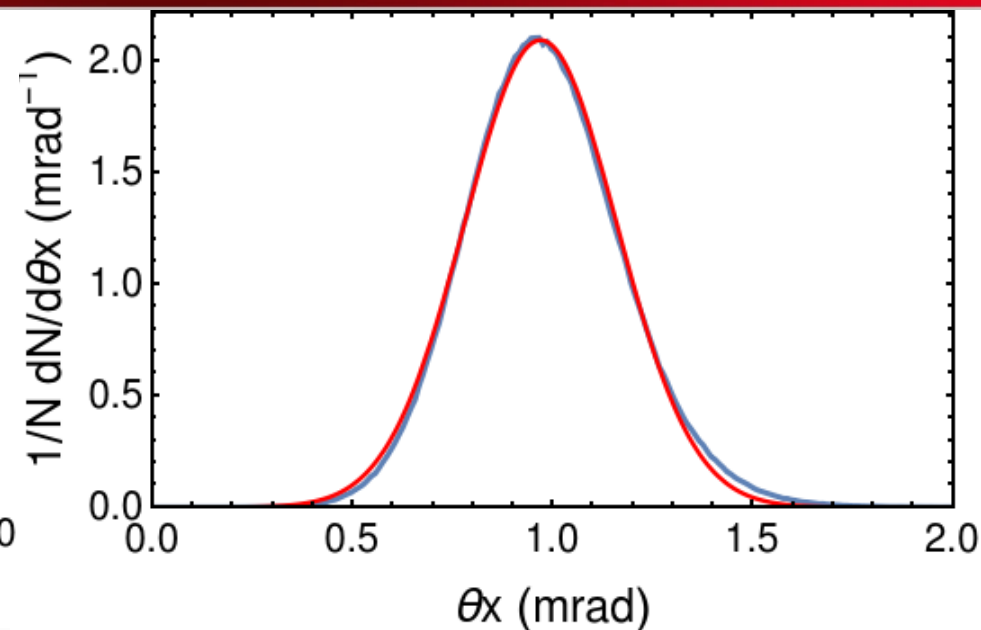
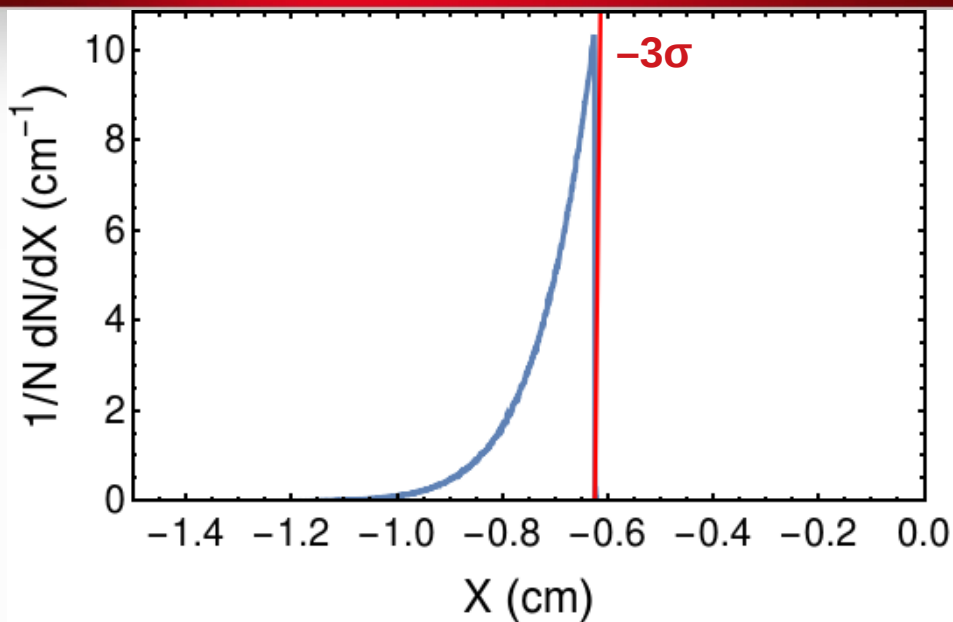


A.I. Sytov, L. Bandiera et al. Eur. Phys. J. C 77, 901 (2017)

D. De Salvador et al. JINST 13, C04006 (2018)

A. Mazzolari, A.I. Sytov, et al. Eur. Phys. J. C 80, 63 (2020)

Setup for simulations and beam at the crystal entrance



Beam Parameters:

- $\epsilon_x = 339$ nm, $\epsilon_y = 35$ nm, $\sigma_e/E = 0.977 \times 10^{-3}$, $E = 6$ GeV
- $\sigma = \sqrt{\beta \epsilon_x}$ (betatron sigma)
- $x_{\text{crystal}} = -3\sigma$, $x_{\text{septum}} = 4\sigma$

Cuts for the extracted beam:

- $x > 4 \sigma = 0.98$ cm
- -4 mrad $< \theta_x < 0$ mrad
- $E = 6.0 \pm 0.1$ GeV
- $N_{\text{turns}} = 100$

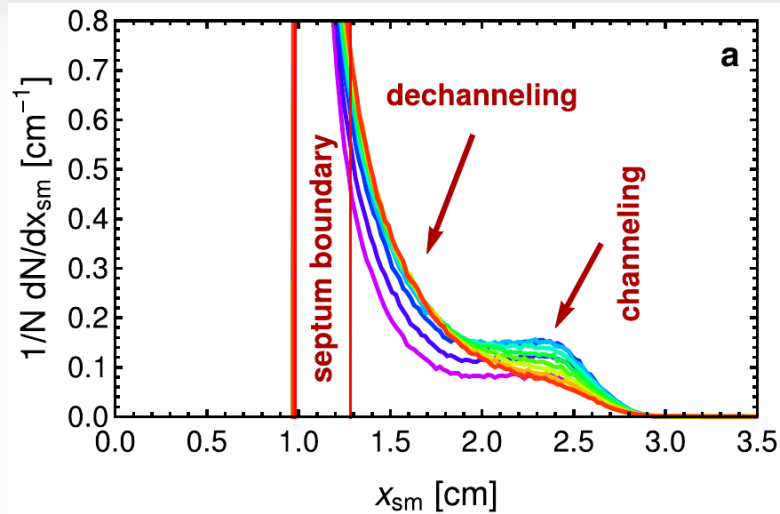
Beam **angular divergence** at the crystal entrance: **0.18 mrad**

Critical channeling angle:
0.07 mrad (Si, (111))

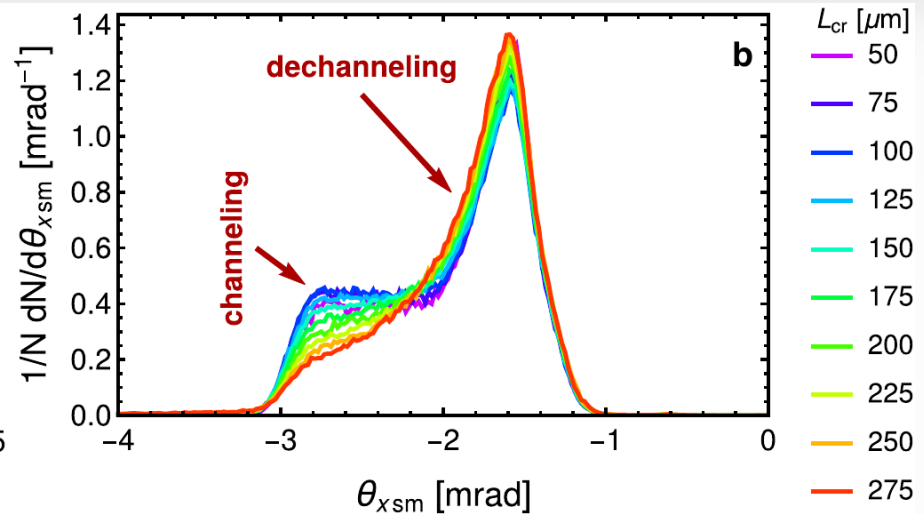
Optimal alignment at -3σ :
0.97 mrad

Crystal-based extraction: old simulation results* with CRYSTALRAD simulation code

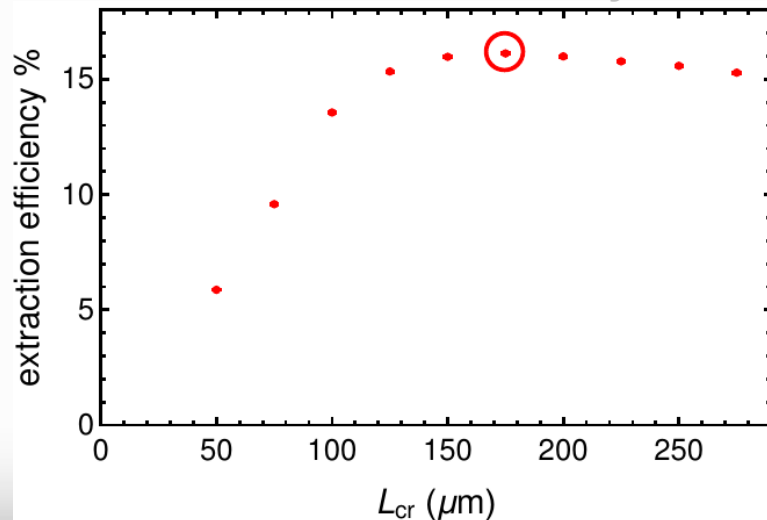
Coordinate distribution of extracted beam



Angular divergence of extracted beam

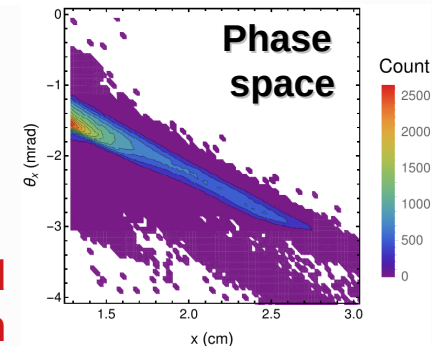


Extraction efficiency



Crystal parameters:

- Si (111)
- bending angle **1.75 mrad**
- Crystal length **0.175 mm**
- Crystal transverse thickness **1 cm**



Maximal extraction efficiency:
16.1 %

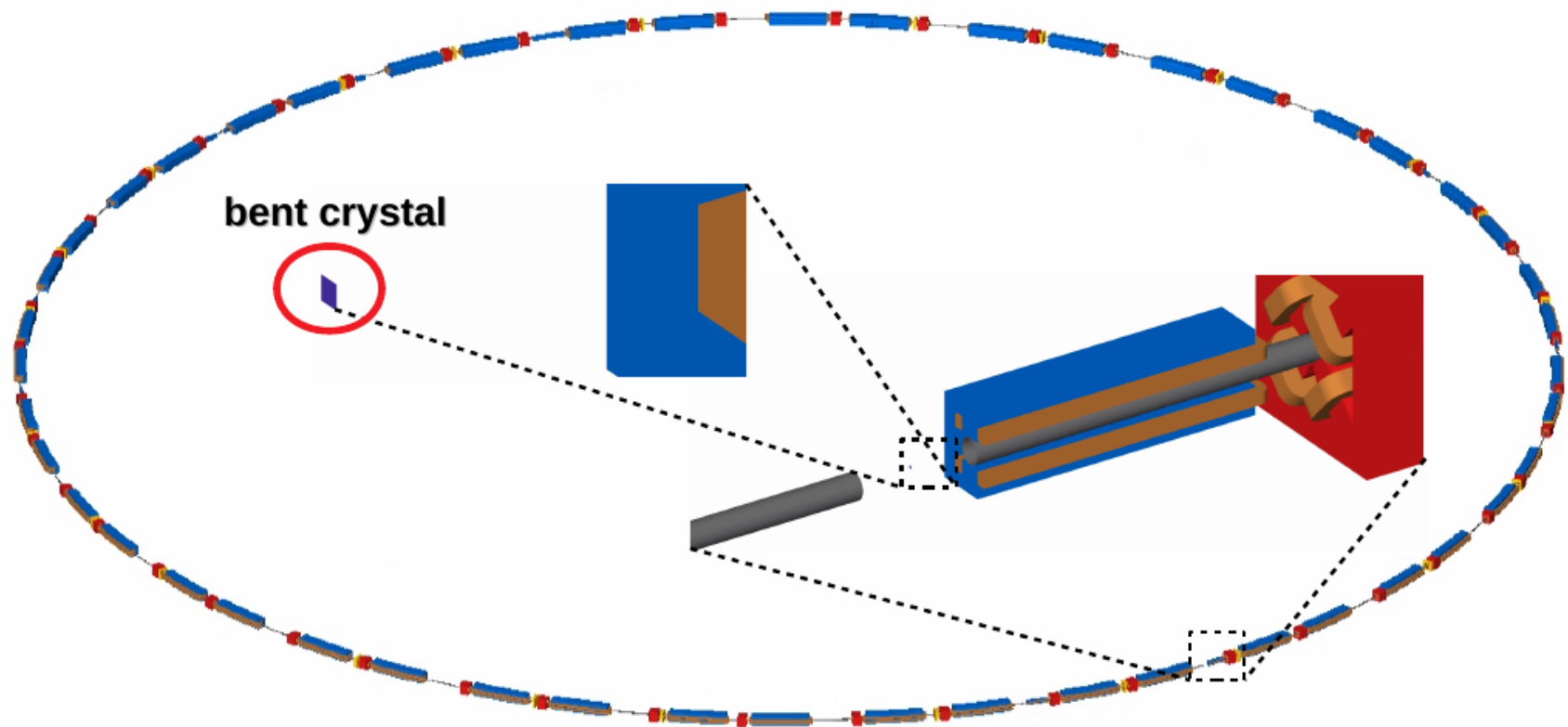
*A. Sytov et al. Eur. Phys. J. C 82, 197 (2022)

My mission to DESY: full simulations with the BDSim simulation code



Purpose of BDSIM:

Beam Delivery Simulation (BDSIM) is a C++ program that utilises the **Geant4 toolkit** to simulate both the **transport of particles in an accelerator** and their **interaction with the accelerator material**. BDSIM is capable of **simulating a wide variety of accelerator components and magnets** with Geant4 geometry dynamically built based on a text input file. **Thick lens accelerator tracking routines** are provided for fast accurate tracking in a vacuum.



Implementation of a new component and a new physics list

```
#include "BDSIMClass.hh" // bdsim interface

#include "CrystalDeflector.hh"
#include "CrystalDeflectorConstructor.hh"

#include "FTFP_BERT.hh"
#include "G4FastSimulationPhysics.hh"
#include "G4StepLimiterPhysics.hh"
#include <iostream>

int main(int argc, char** argv)
{
    // construct an instance of bdsim
    BDSIM* bds = new BDSIM();

    // Physics list
    G4VModularPhysicsList* physicsList = new FTFP_BERT;
    // -- Create helper tool, used to activate the fast simulation:
    G4FastSimulationPhysics* fastSimulationPhysics = new G4FastSimulationPhysics();
    fastSimulationPhysics->BeVerbose();
    // -- activation of fast simulation for particles having fast simulation models
    // -- attached in the mass geometry:
    fastSimulationPhysics->ActivateFastSimulation("e-");
    fastSimulationPhysics->ActivateFastSimulation("e+");
    // -- Attach the fast simulation physics constructor to the physics list:
    physicsList->RegisterPhysics( fastSimulationPhysics );
    physicsList->RegisterPhysics(new G4StepLimiterPhysics());
    bds->RegisterUserPhysicsList(physicsList);

    // register a custom component by name udipole with a user-provided constructor
    // BDSIM will delete the constructor at the end.
    bds->RegisterUserComponent("crystaldeflector", new CrystalDeflectorConstructor());

    // construct geometry and physics
    bds->Initialise(argc, argv);
    if (!bds->Initialised()) // check if there was a problem.
        {std::cout << "Intialisation failed" << std::endl; return 1;}

    bds->BeamOn(); // run the simulation
    delete bds;    // clean up
    return 0;     // exit nicely
}
```

CrystalDeflectorConstructor.cc

```
BDSAcceleratorComponent* crystal = new CrystalDeflector(element->name,
                                                         element->l*CLHEP::m,
                                                         element->xsize*CLHEP::m,
                                                         element->ysize*CLHEP::m,
                                                         element->materialThickness*CLHEP::m,
                                                         element->axisX,
                                                         element->axisY,
                                                         element->axisZ,
                                                         horizontalWidth*CLHEP::m,
                                                         bendingAngle,
                                                         material,
                                                         vacuumMaterial,
                                                         crystalLattice,
                                                         region,
                                                         colour,
                                                         radiationModel);

D12H: drift, l=0.4125;
CR1: usercomponent, typeName="crystaldeflector",
l=0.4125, xsize=1*cm, ysize=1*cm,
materialThickness=0.175*mm, offsetX=-1.126046*cm,
offsetY=0*mm, axisX=0.000, axisY = -0.00097, axisZ = 0.,
horizontalWidth=1*m, material="G4_Si",
vacuumMaterial="vacuum",
userParameters="crystalRegion:crystal1
crystalBendingAngle:0.00175 crystalLattice:(111)
colour:decapole radiationModel:false"; dump1: dump,
l=1*mm, horizontalWidth=4*cm,
apertureType="rectangular",offsetX=2.98*cm;
D1R: drift l=@ 495.
```

CrystalDeflector.cc

```
void CrystalDeflector::BuildCrystal()
{
    //build crystal solid
    G4Box* crystalSolid = new G4Box(name + "_crystal_solid",
        crystalXSize * 0.5,
        crystalYSize * 0.5,
        crystalMaterialThickness * 0.5);
    RegisterSolid(crystalSolid); // for deletion by bdsim

    // make a logical volume for the crystal
    G4LogicalVolume* crystalLV = new G4LogicalVolume(crystalSolid,
        crystalMaterial,
        name + "_crystal_lv");

    // visualisation attributes - make it nicely visible
    G4VisAttributes* crystalVis = new G4VisAttributes(*BDSColours::Instance()->GetColour(crystalcolour));
    crystalVis->SetVisibility(true);
    crystalLV->SetVisAttributes(crystalVis);
    RegisterVisAttributes(crystalVis); // for deletion by bdsim
    RegisterLogicalVolume(crystalLV); // for deletion by bdsim

    G4RotationMatrix* crystalRM = new G4RotationMatrix();
    crystalRM->rotateX(crystalAxisX);
    crystalRM->rotateY(crystalAxisY);
    crystalRM->rotateZ(crystalAxisZ);
    RegisterRotationMatrix(crystalRM); // for deletion by bdsim
    G4double crystalZPos = 0*CLHEP::cm;
    G4ThreeVector crystalPos = G4ThreeVector(0,0, crystalZPos);

    //physical volume
    auto crystalPV = new G4PVPlacement(crystalRM,
        crystalPos,
        crystalLV,
        name + "_crystal",
        containerLogicalVolume,
        false,
        0,
        checkOverlaps);
    RegisterPhysicalVolume(crystalPV); // for deletion by bdsim

    G4Region* crystalRegion = new G4Region(crystalRegionName);
    crystalRegion->AddRootLogicalVolume(crystalLV);

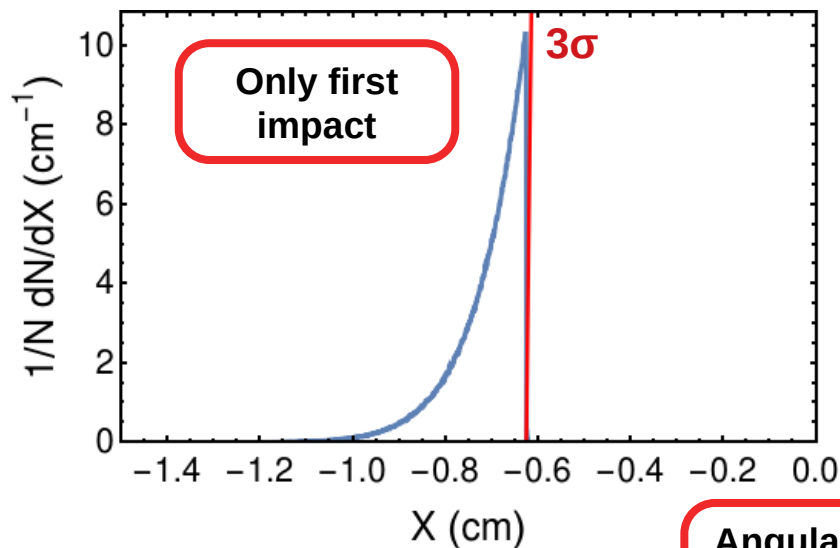
    //create the channeling model for this region
    G4ChannelingFastSimModel* ChannelingModel = new G4ChannelingFastSimModel("ChannelingModel", crystalRegion);
    //activate the channeling model
    ChannelingModel->Input(crystalMaterial, crystalLattice);
    //setting bending angle of the crystal planes (default is 0)
    ChannelingModel->GetCrystalData()->SetBendingAngle(crystalBendingAngle, crystalLV);

    if(crystalRadiationModel){ChannelingModel->RadiationModelActivate();}
```

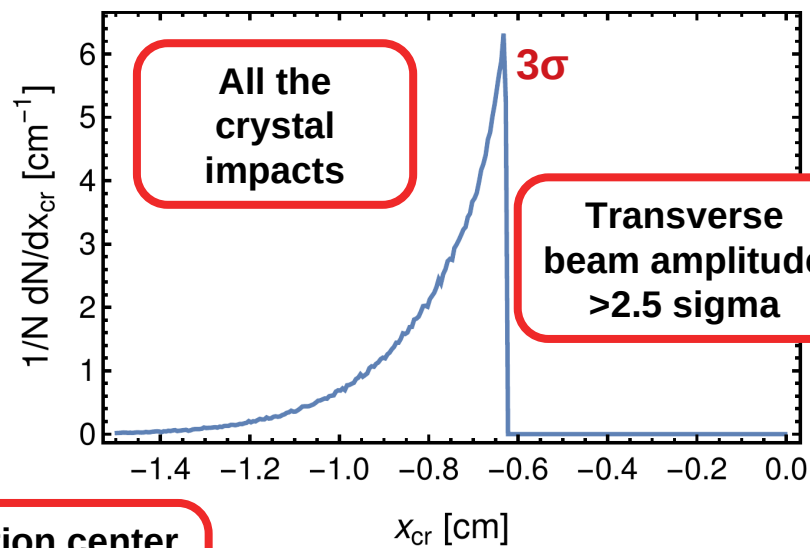
Crystal impact

(both transverse and energy spread is taken into account)

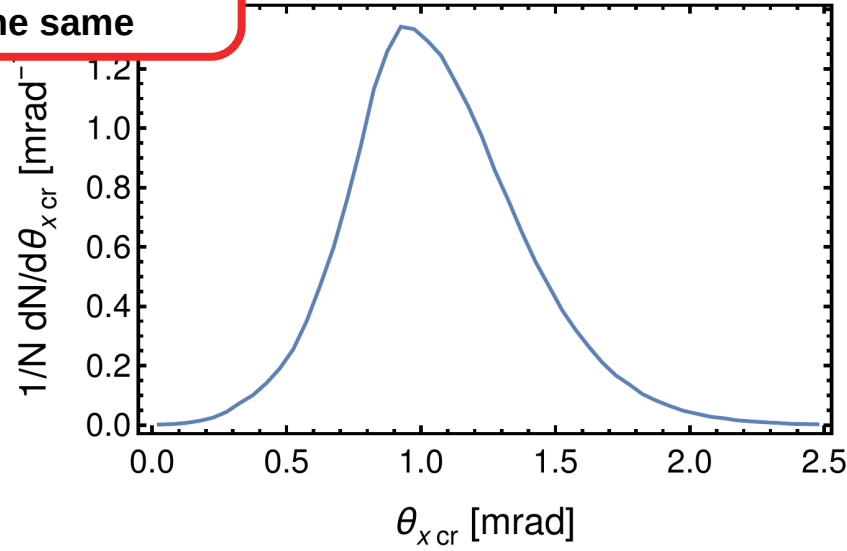
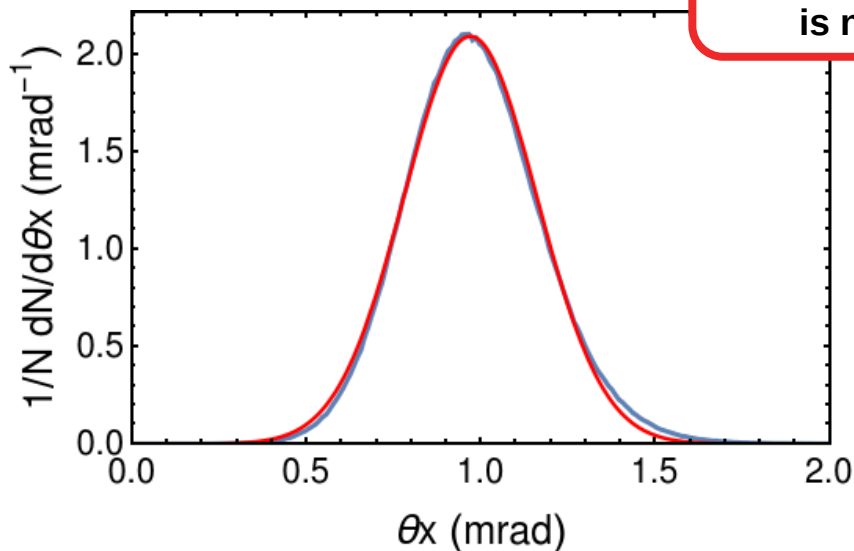
Old paper*



BDSim

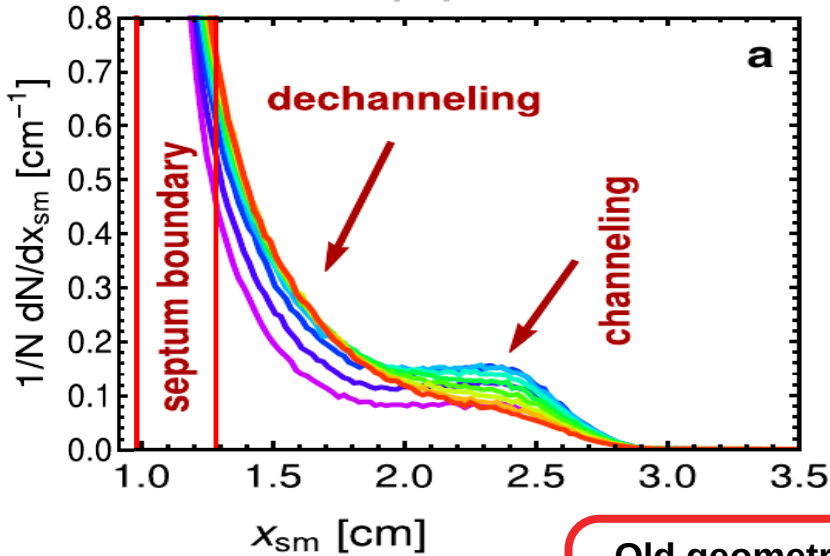


Angular distribution center is nearly the same

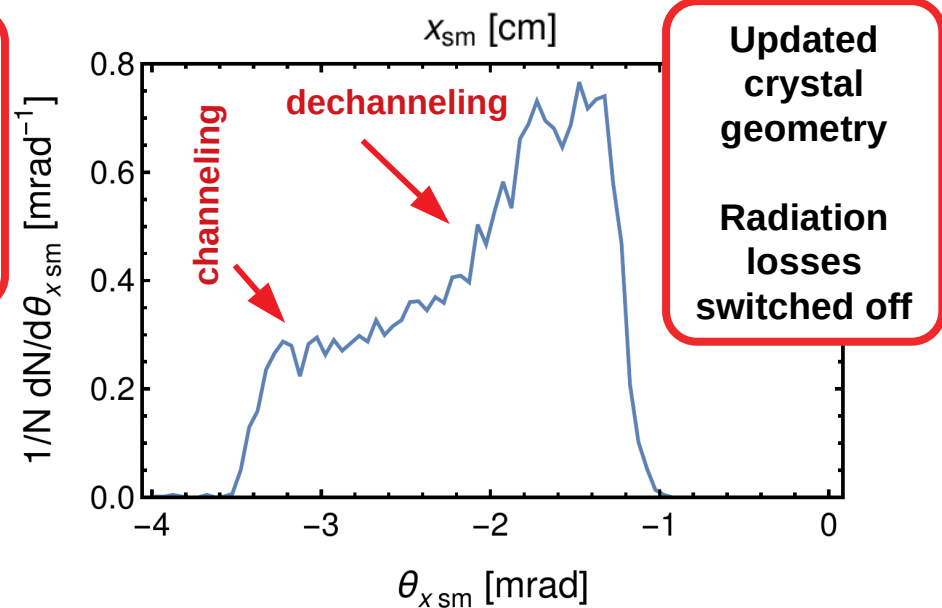
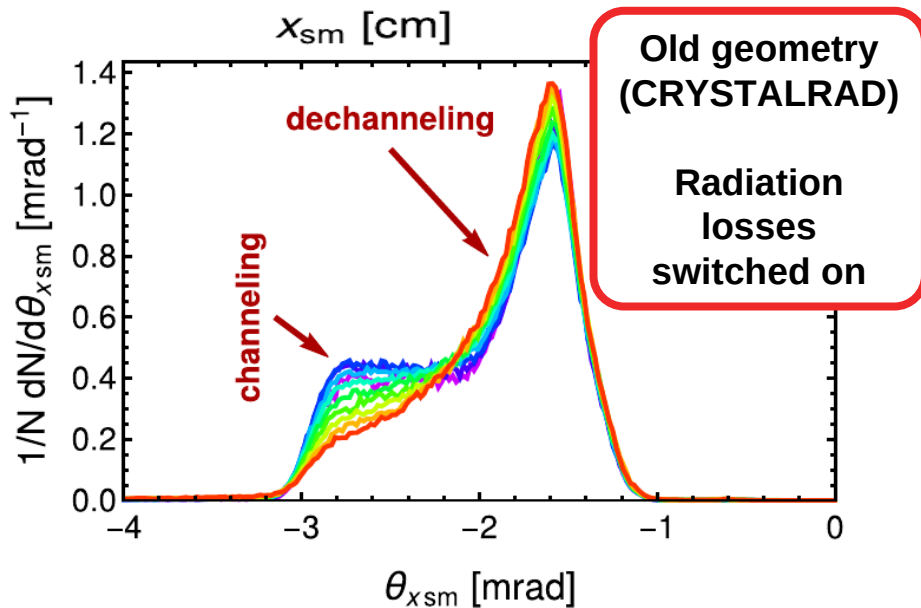
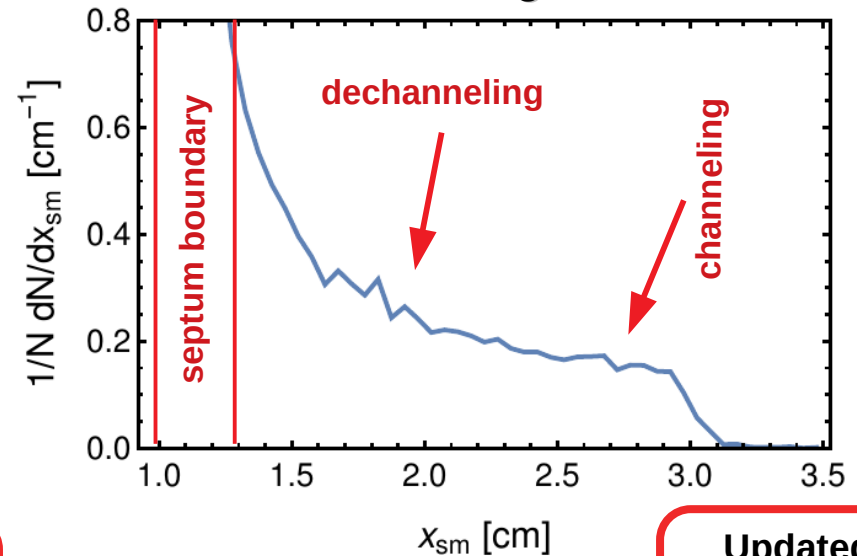


Crystal-based extraction: simulation results distributions at the septum magnet entrance

Old paper*



BDSim & ChannelingFastSimModel



Summary and Future plans 2024

parameters* (still valid)

Bent crystal thickness	175 μm
Bent crystal bending angle	1.75 mrad
Bent crystal transverse position	-0.63 cm
Bent crystal angular alignment	0.97 mrad
Septum magnet transverse position	0.98 cm

Main part of the **beam** will **not touch** the **crystal**

5% of the **beam** will **enter** into the **septum magnet**



~50 pC can be **extracted**

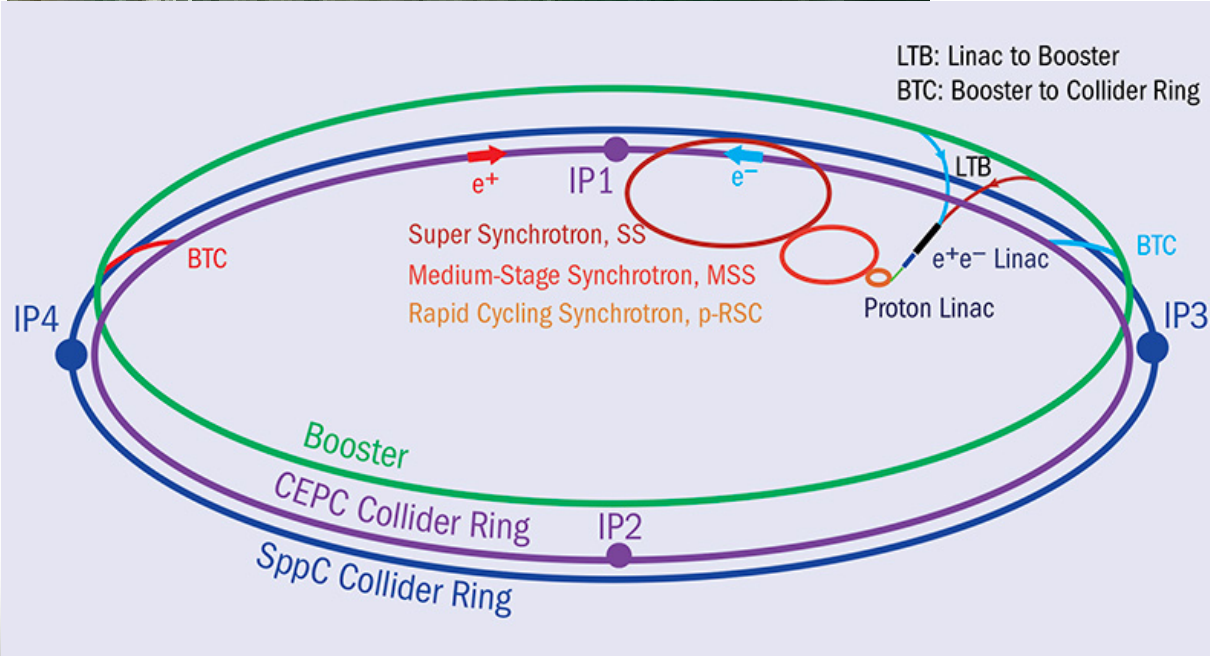
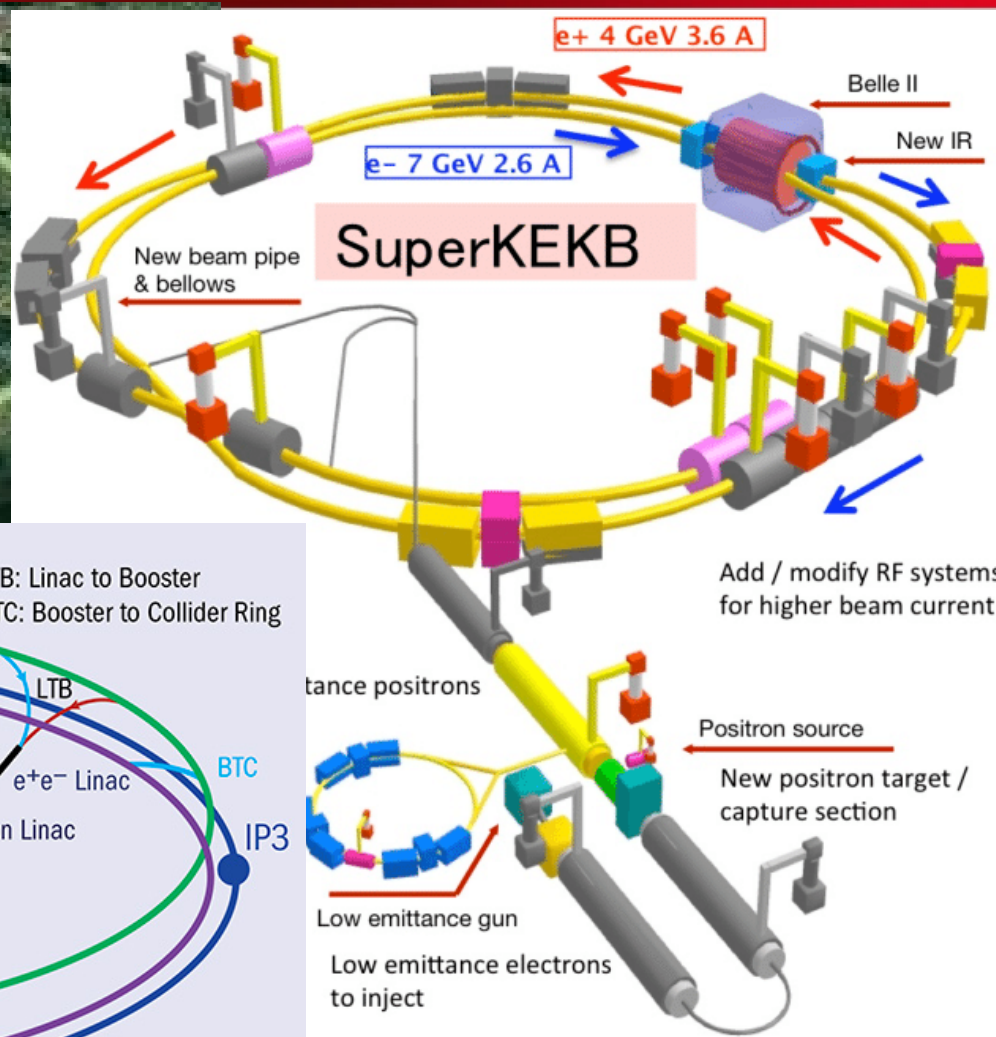
Future plans

- **Turn on cavities** and **radiation losses** in the **crystal**
- **Track** the particles also in the **extraction line**
- Calculate the **beam emittance** and **beam charge** at the extraction line exit
- Simulation of **ionization losses** in the crystal to estimate the radiation damage if any
- Further **optimization** of the crystal geometry and location
- Consider **other crystal materials/crystalline effects**

Where the crystal-based extraction of electrons can be applied?



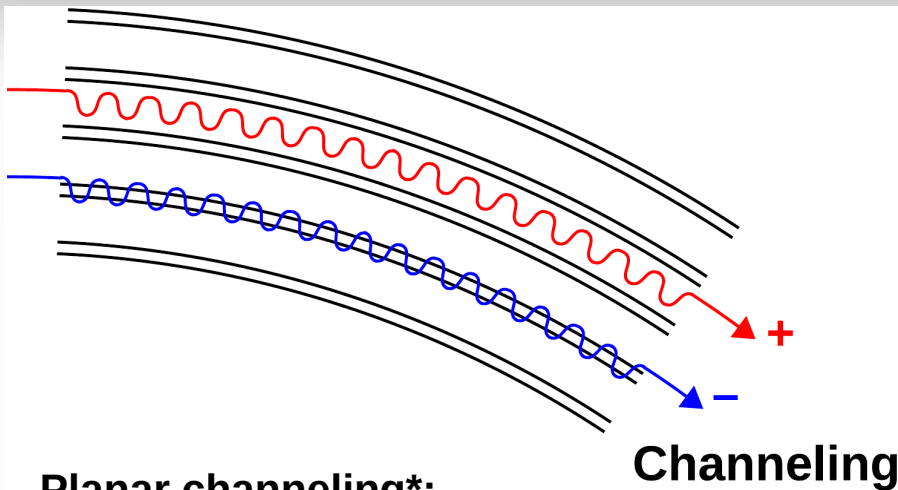
Where the crystal-based extraction of electrons can be applied?





Thank you for attention!

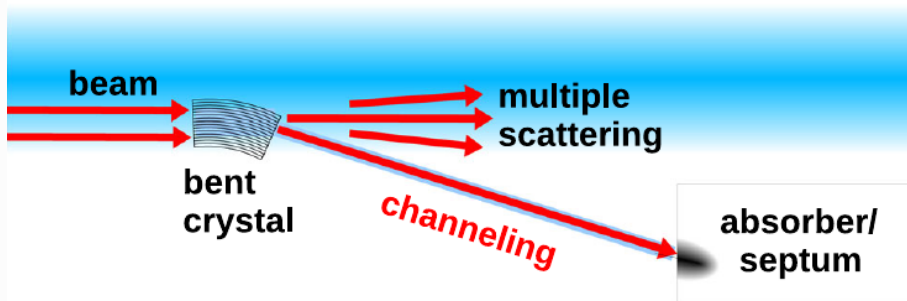
Crystal-based extraction: the idea



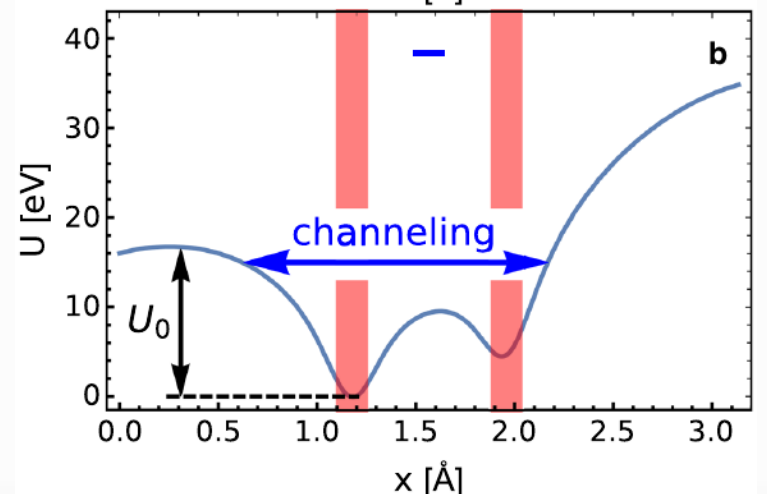
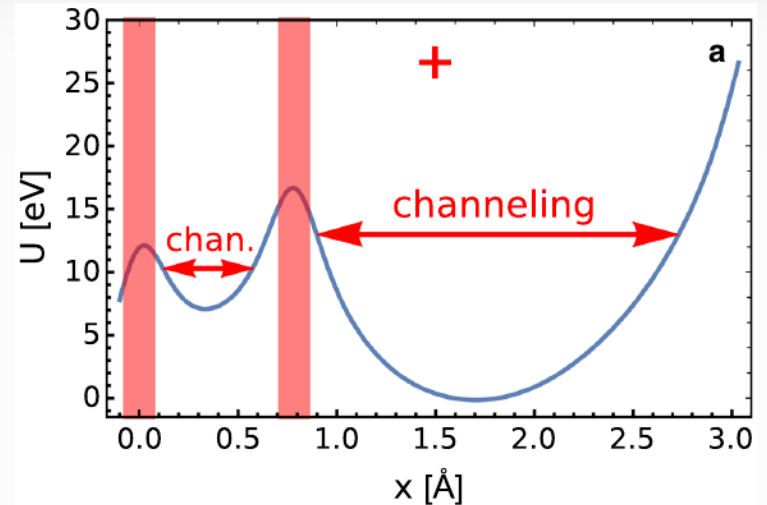
Planar channeling*:

● Charge particle penetration through a monocrystal along its atomic planes

Crystal-based extraction**



Interplanar potential

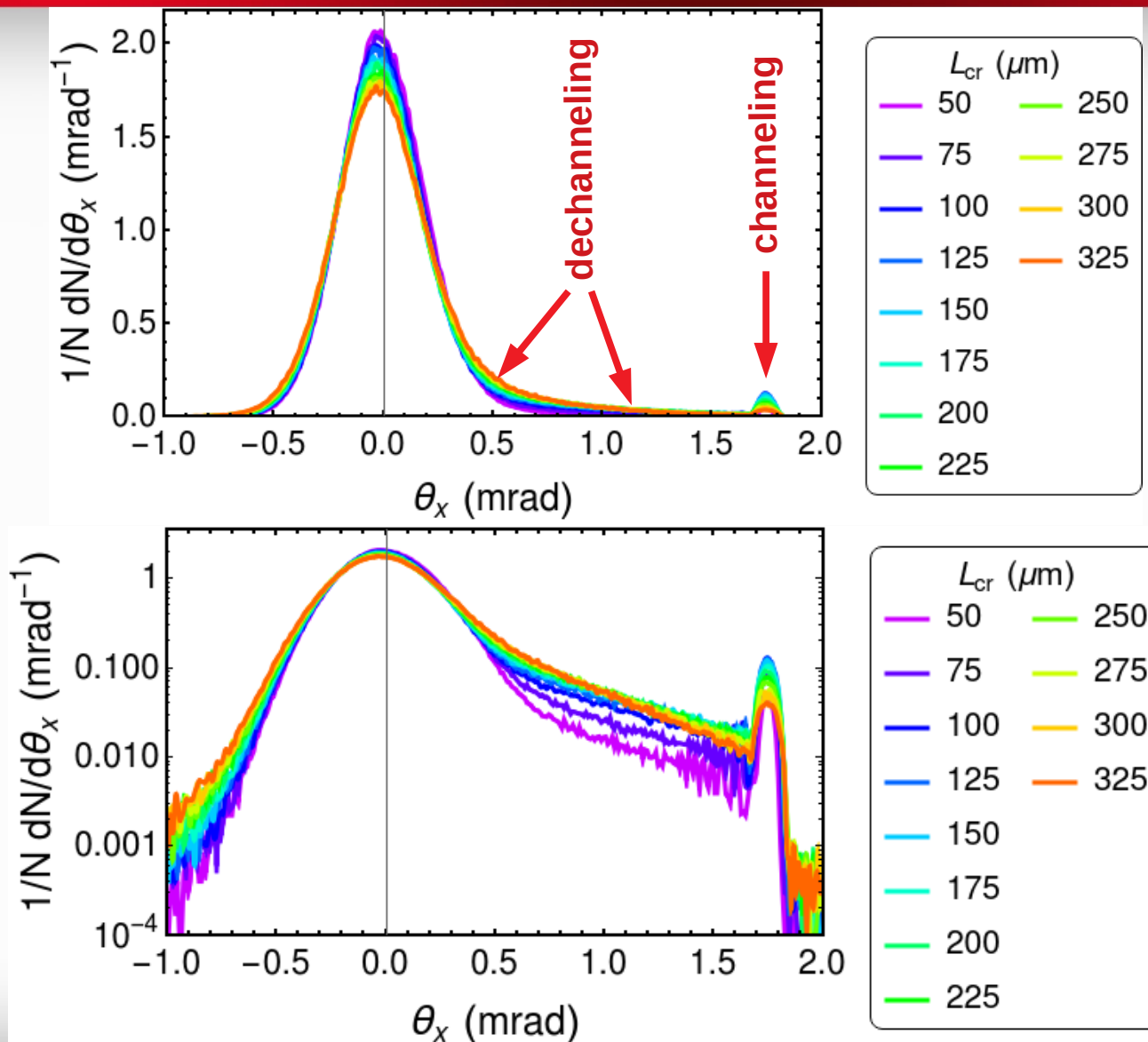


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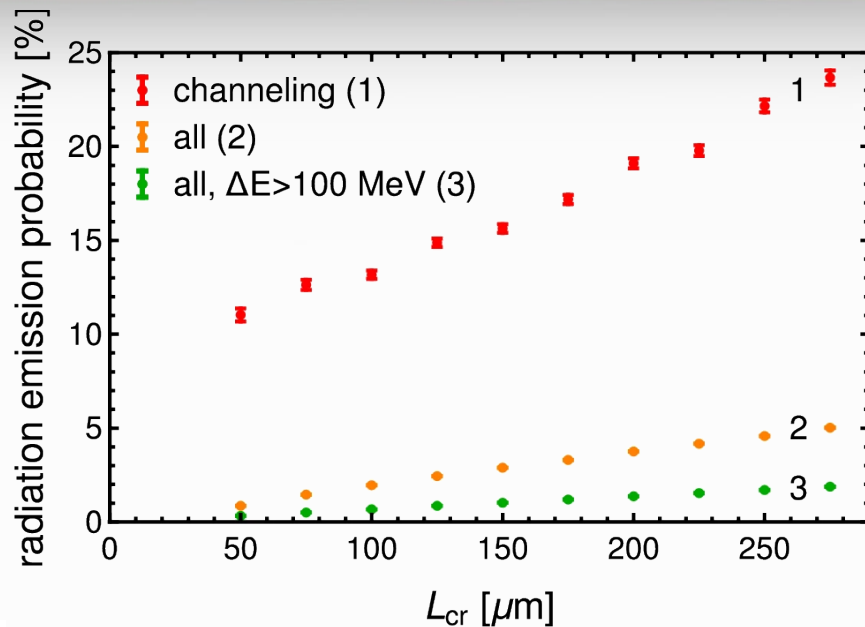
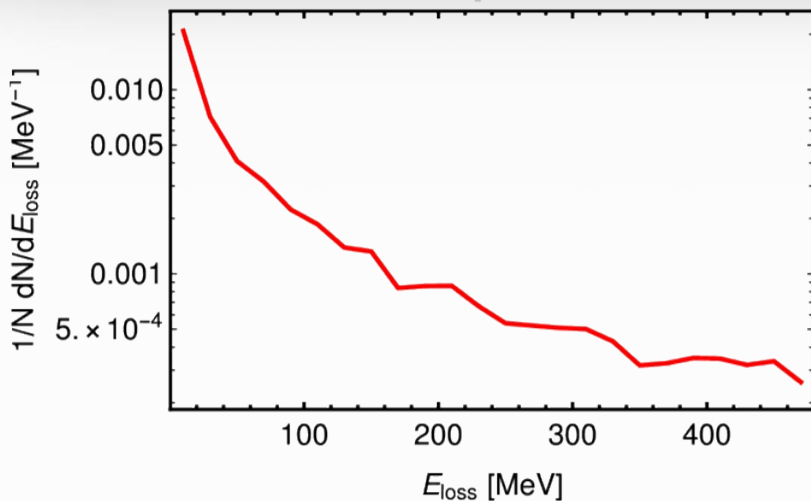
**A. Sytov et al., Eur. Phys. J. C (2022) 82:197

Simulated angular distributions of deflected beam

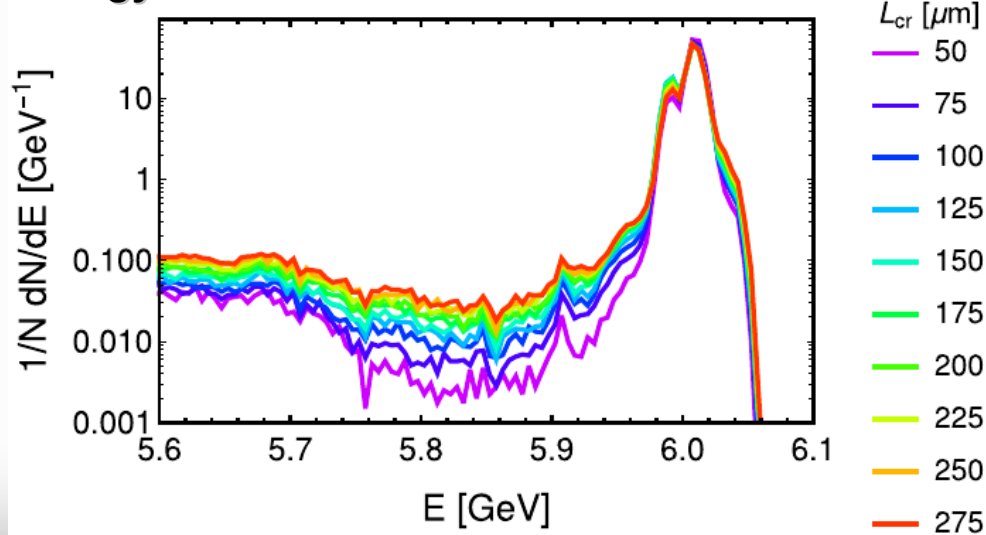


Crystal-based extraction simulations: energy losses

Radiation spectrum



Energy distribution of the extracted beam



Radiation emission probability as function of the crystal thickness for **(red)** channeled particles, for **(yellow)** all particles and for **(green)** particles with radiation energy losses exceeding 100 MeV.

Energy remains within **RF bucket**